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SEP 24 2004

Docket Number (Optional) OKI.639		Application Number 10/768,185
Applicant(s) Toshio Ito		
Filing Date 02/02/2004	Group Art Unit 2811	

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>[Signature]</i>	A	6,459,111	10/2002	NATORI et al.			

U.S. PATENT APPLICATION PUBLICATIONS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER <i>[Signature]</i>	DATE CONSIDERED <i>12/12/04</i>
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OKI.639

Application Number

NEW 10/768185

Applicant(s)

Toshio ITO

Filing Date

February 2, 2004

Group Art Unit

To Be Assigned

U.S. PATENT DOCUMENTS

[illegible]

FOREIGN PATENT DOCUMENTS

[illegible]

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

S	c	S.Y. Lee et al., "A FRAM technology using 1T1C and triple metal layers for high performance and high density FRAMs", 1999 Symposium on VLSI Technology Digest of Technical Papers, pgs. 141-142.

DATE CONSIDERED

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